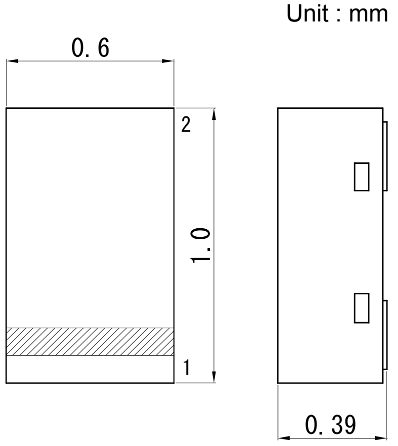
DZ2636000L

Silicon epitaxial planar type

For constant voltage / For surge absorption circuit
DZ27360 in ML2 type package



1. Cathode
2. Anode

Panasonic	ML2-N3-B
JEITA	—
Code	SOD-882

■ Features

- Excellent rising characteristics of zener current IZ
- Low zener operating resistance RZ
- Halogen-free / RoHS compliant
  (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol : JG

■ Packaging

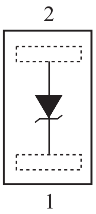
Embossed type (Thermo-compression sealing) : 10 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Repetitive peak forward current	IFRM	200	mA
Total power dissipation [*1]	PT	100	mW
Electrostatic discharge [*2]	ESD	±8	kV
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

Note) *1 PT = 100 mW achieved with a printed circuit board.
*2 Test method:IEC61000_4_2
(C = 150 pF , R = 330 Ω , Contact discharge : 10 times)

Internal Connection



■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	VF	IF = 10 mA			1.0	V
Zener voltage [*1, *2]	VZ	IZ = 2 mA	34.20		37.80	V
Zener operating resistance	RZ	IZ = 2 mA			250	Ω
Zener rise operating resistance	RZK	IZ = 0.5 mA			250	Ω
Reverse current	IR	VR = 27 V			0.05	µA
Temperature coefficient of zener voltage [*3]	SZ	IZ = 2 mA		35.4		mV/°C

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for Diodes.
2. Absolute frequency of input and output is 5 MHz.
3. *1 The temperature must be controlled 25 °C for VZ mesurement.
VZ value measured at other temperature must be adjusted to VZ (25 °C)
*2 VZ guaranteed 20 ms after current flow.
*3 Tj = 25 °C to 150 °C